

- Qualified for Automotive Applications
 - Wide Input Voltage Range: 3.1V-50V
 - Low Shutdown Current 3.9uA
 - Low Quiescent Operating Current: 415uA
 - +/- 1.5% Feedback Reference Voltage
 - Adjustable Switching Frequency: 100KHz to 2.2MHz
 - Integrated Frequency Dither for EMI Mitigation
 - External Frequency Synchronic
 - External Compensation
 - Pulse Skipping Mode
 - Supports additional Slope Compensation
 - 14ms Internal Soft-start Time
 - Integrated Protection Feature
 - Constant Peak-Current Protection Threshold Over Input Voltage
 - Output Overvoltage Protection
 - Adjustable Under-voltage Lockout
 - Hiccup Over Load Protection
 - Thermal Shutdown Protection:165°C
 - MSOP-10L(3mm*3mm)
-
- Multi-output Flyback
 - LED Bias Supply
 - Portable Speaker Supply
 - Battery Powered Boost/Flyback/SEPIC application

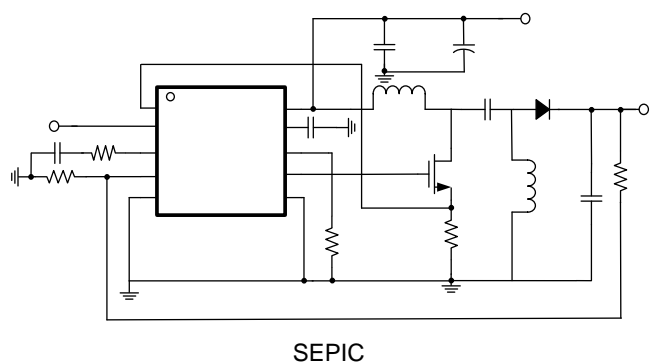
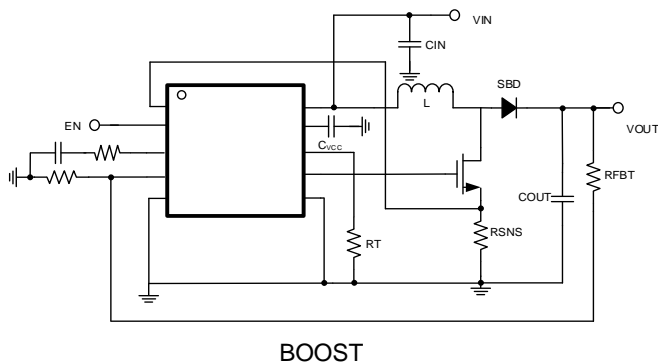
The SCT81621 device is a wide input, non-synchronous boost controller. The device can be used in Boost, SEPIC and Flyback converters.

The switching frequency of the SCT81621 device can be adjusted to any value between 100kHz and 2.2MHz by using a single external resistor or by synchronizing it to an external clock. Current mode control provides superior bandwidth and transient response in addition to cycle-by-cycle current limiting. Current limit is adjustable through an external resistor.

The SCT81621 is an Electromagnetic Interference (EMI) friendly controller with implementing optimized design for EMI reduction. The SCT81621 features Frequency Spread Spectrum (FSS) with $\pm 6\%$ jittering span of the switching frequency and modulation rate 1/512 of switching frequency to reduce the conducted EMI.

The SCT81621 device has built-in protection features such as thermal shutdown, short-circuit protection and overvoltage protection. Power-saving shutdown mode reduces the total supply current to 3.9 μ A. Integrated current slope compensation simplifies the design and, if needed for specific applications, can be increased using a single resistor.

The device is available in a MSOP-10L(3mm*3mm) Package.



SCT81621

NOTE: Page numbers for previous revisions may differ from page numbers in the current version

Revision 1.0: Released to Market

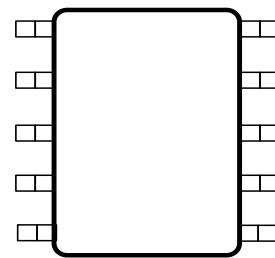
Revision 1.1: Update UVLO Equation

PART NUMBER	PACKAGE MARKING	PACKAGE DISCRIPTION
SCT81621MRD	1621	10-Lead 3mmx3mm Plastic MSOP

1) For Tape & Reel, Add Suffix R (e.g. SCT81621MRDR)

Over operating free-air temperature unless otherwise noted⁽¹⁾

DESCRIPTION	MIN	MAX	UNIT
VIN, UVLO_EN	-0.3	62	V
VCC, DR	-1	6.6	V
ISEN, COMP, FB, FA/SYNC/SD	-5	5.5	V
Peak Driver Output Current		1 ⁽²⁾	A
Junction temperature ⁽²⁾	-40	150	C
Storage temperature T _{STG}	-65	150	C



Top View: 10-Lead Plastic MSOP 3mmx3mm

- (1) Stresses beyond those listed under Absolute Maximum Rating may cause device permanent damage. The device is not guaranteed to function outside of its Recommended Operation Conditions.
- (2) Guaranteed by design, not tested in productions.
- (3) The IC includes over temperature protection to protect the device during overload conditions. Junction temperature will exceed 170°C when over temperature protection is active. Continuous operation above the specified maximum operating junction temperature will reduce lifetime.

NAME	NO.	DESCRIPTION
ISEN	1	Current sense input pin. Connect to the positive side of the current sense resistor through a short path.
UVLO_EN	2	Undervoltage lockout programming pin. The converter start-up and shutdown levels can be programmed by connecting this pin to the supply voltage through a resistor divider. This pin must not be left floating. Connect to VIN pin if not used.
COMP	3	Output of the internal transconductance error amplifier. Connect the loop compensation components between this pin and ground.
FB	4	Inverting input of the error amplifier. Connect a voltage divider from the output to this pin to set output voltage. The device regulates FB voltage to the internal reference value of 1.275V typical.
AGND	5	Analog ground pin.
FA/SYNC/SD	6	Switching frequency setting pin. The switching frequency is programmed by a single resistor between this pin and AGND. The internal clock can be synchronized to an external clock. A high level on this pin for 30 μ s will turn the device off and the device will then draw 3.9 μ A from the supply typically.

SCT81621

$V_{IN}=12V$, $T_J=-40^{\circ}C\sim 125^{\circ}C$, typical values are tested under $25^{\circ}C$.

SYMBOL	PARAMETER	TEST CONDITION	MIN	TYP	MAX	UNIT
Power Supply and Output						
V_{IN}	Operating input voltage		3.1		50	V
V_{IN_UVLO}	Input UVLO Hysteresis	V_{IN} rising		2.8 160		V mV
I_{SD}	Shutdown current	$V_{FA}/SYNC/SD=5V$ or $V_{UVLO_EN}=0$		3.9	8	μA
I_Q	Quiescent current from V_{IN}	no load, no switching, $V_{FB}=2V$		415		μA
$I_{SUPPLY}^{(1)}$	Supply Current	$R_{FA}/SYNC/SD=47.5k$, switching, no load and without external MOSFET		2		mA
VCC Power						
V_{CC}	Internal linear regulator	$V_{IN}>7V$		6.1		V
V_{CC_uvlo}				2.85		V
$V_{CC_uvlo_hys}$				75		mV
I_{VCC}	VCC Sourcing current limit		20	70		mA
UVLO/EN						
$V_{UVLOSEN}$	Under voltage Lockout reference voltage	V_{UVLO} ramping up	1.34	1.42	1.5	V
I_{UVLO}	UVLO source current		3	4.75	6.5	μA
V_{UVLOSD}	UVLO shut down voltage	V_{UVLO} ramping down	0.55	0.65	0.75	V
Reference and Control Loop						
V_{REF}	Reference voltage of FB		1.256	1.275	1.294	V
I_{FB}	FB pin leakage current	$V_{FB}=1V$			100	nA
G_{EA}	Error amplifier trans-conductance	$V_{COMP}=1.5V$	190	390	590	μS
I_{COMP_SRC}	Error amplifier maximum source current	$V_{FB}=V_{REF}-200mV$, $V_{COMP}=1.5V$	340	560	710	μA
I_{COMP_SNK}	Error amplifier maximum sink current	$V_{FB}=V_{REF}+200mV$, $V_{COMP}=1.5V$	-150	-95	-40	μA
V_{COMP_H}	COMP high clamp	$V_{FB}=0.8V$	1.9	2.55	3.2	V
V_{COMP_L}	COMP low clamp	$V_{FB}=1.7V$	0.4	0.88	1.2	V
Gate Driver						
$R_{DS(on)_TOP}$	Driver switch on resistance(top)	$I_{DR}=0.1A$		3		
$R_{DS(on)_LOW}$	Driver switch on resistance(bottom)	$I_{DR}=0.1A$		2		
Current Sense						
V_{sense}	Current sense threshold		120	146	170	mV
$V_{SL}^{(2)}$	Internal compensation Ramp voltage			90		mV
$C_{HICC-DEL}$	Hiccup mode activation delay	Clock cycles with current limiting before hiccup off-time activated (SS_done)		64		cycles

$V_{IN}=12V$, $T_J=-40^{\circ}C\sim 125^{\circ}C$, typical values are tested under $25^{\circ}C$.

SYMBOL	PARAMETER	TEST CONDITION	MIN	TYP	MAX	UNIT
C_{HICCUP}	Hiccup mode off-time after activation	Clock cycles with no switching followed by SS release		32768		cycles
Soft start						
T_{SS}	Soft-start Time			14		ms
Switching Frequency						
F_{SW}	Switching frequency	$R_{FA/SYNC/SD}=47.5k$	345	400	455	kHz
F_{SS}	Frequency Spread Range			6		%
SYN_{HI}	Threshold for Synchronization on FA/SYNC/SD pin	Synchronization voltage rising		1.27	1.45	V
SYN_{LO}		Synchronization voltage falling	0.58	0.68		V
D_{MAX}	Maximum Duty Cycle	$R_{FA/SYNC/SD}=47.5k$	85	91		%
t_{ON_MIN}	Minimum on-time	$F_{sw}=400kHz$		250		ns
V_{SD_HI}	Shutdown signal threshold on FA/SYNC/SD pin	Shutdown voltage rising		1.27	1.45	V
V_{SD_LO}		Shutdown voltage falling	0.57	0.68		V
I_{SD_LKG}	FA/SYNC/SD pin Leakage	$V_{SD}=5V$			1	uA
Protection						
$V_{OVTH}^{(3)}$	FB overvoltage threshold	FB rising	25	85	135	mV
		Hysteresis	30	80	130	mV

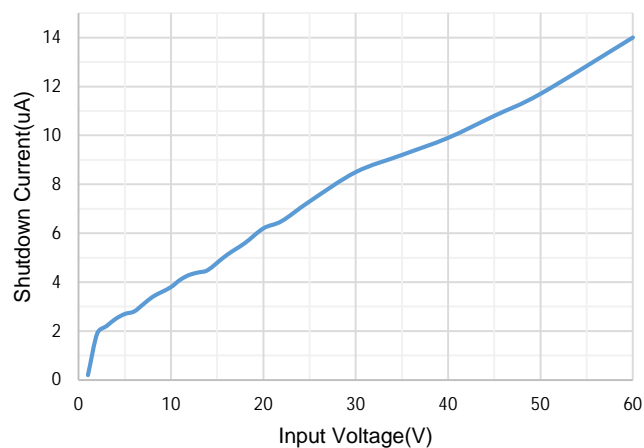


Figure 1. ISD vs. Input Voltage

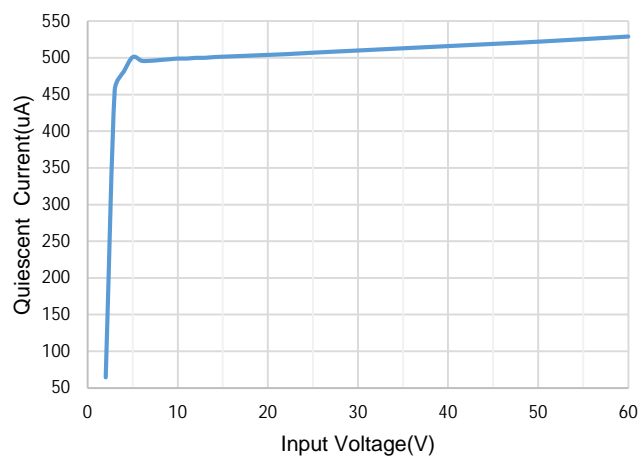


Figure 2. IQ vs. Input Voltage

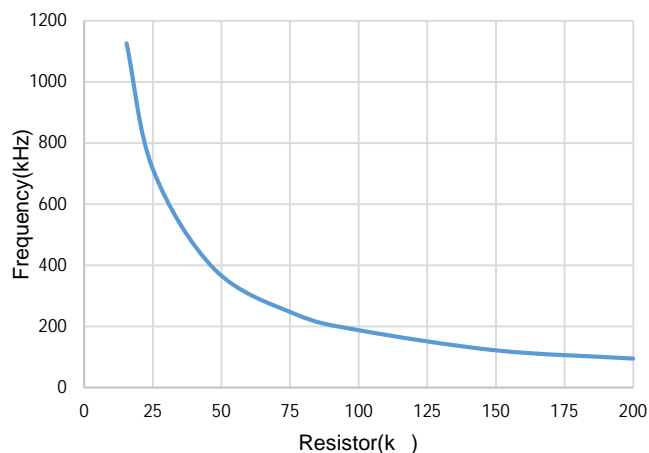


Figure 3. Switching Frequency vs. RT

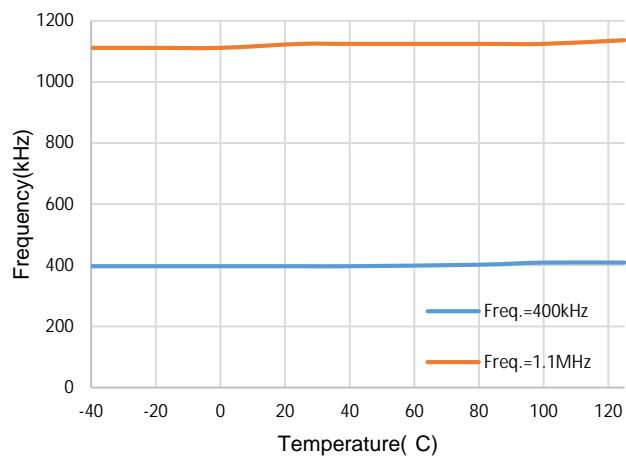


Figure 4. Switching Frequency vs. Temperature

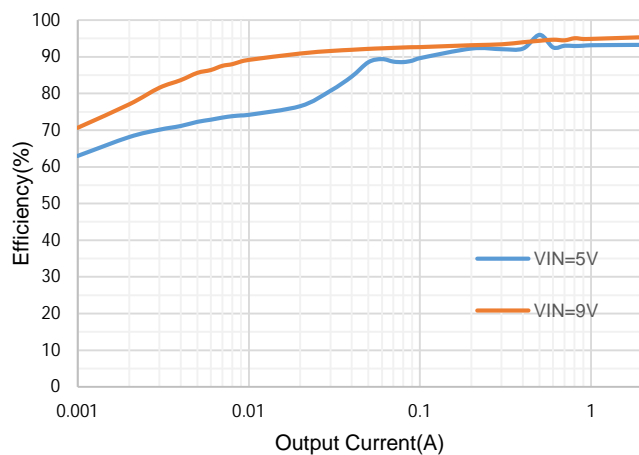


Figure 5. Efficiency vs Load Current, Boost, VOUT=12V

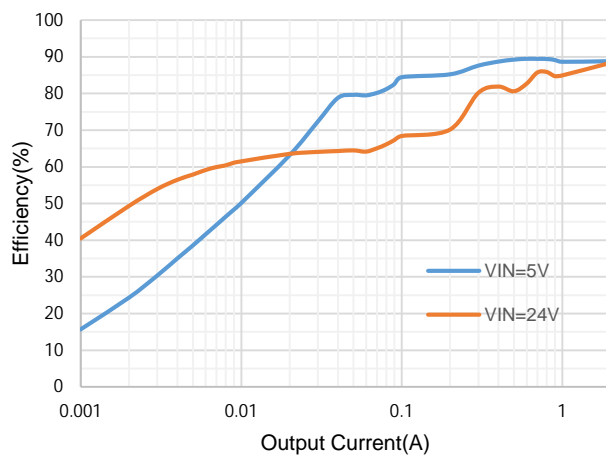


Figure 6. Efficiency vs Load Current, Sepic, VOUT=12V

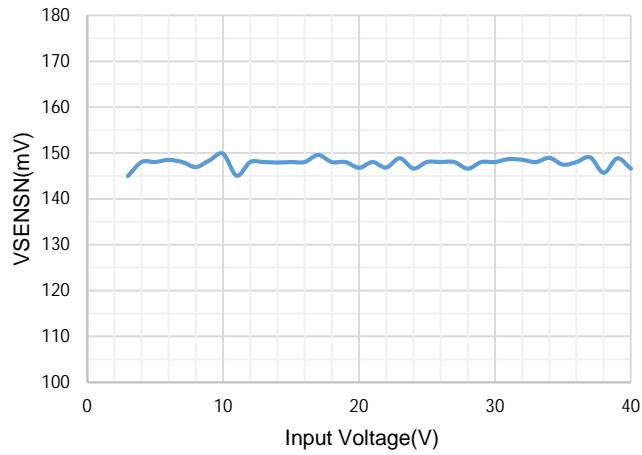


Figure 7. VSENSN vs. Input Voltage

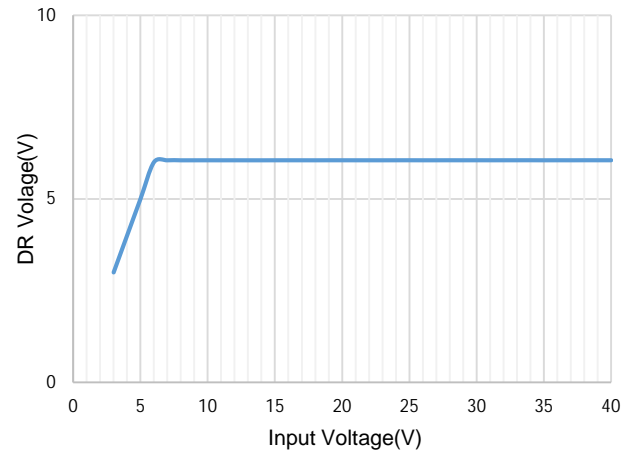


Figure 8. DR Voltage vs. Input Voltage

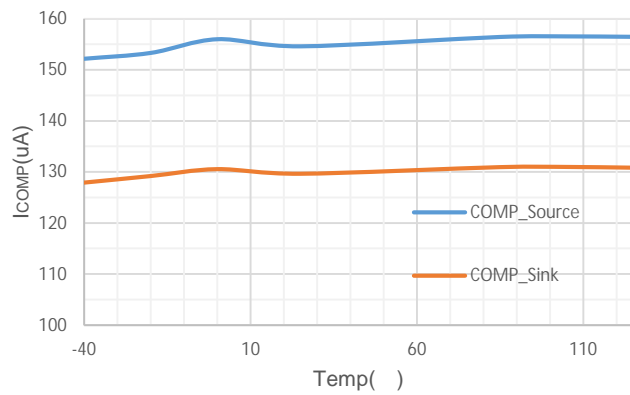


Figure 9. COMP Current vs. Temperature

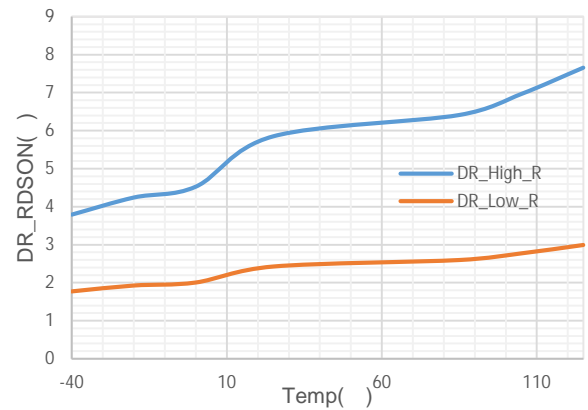


Figure 10. DR Resistance vs. Temperature

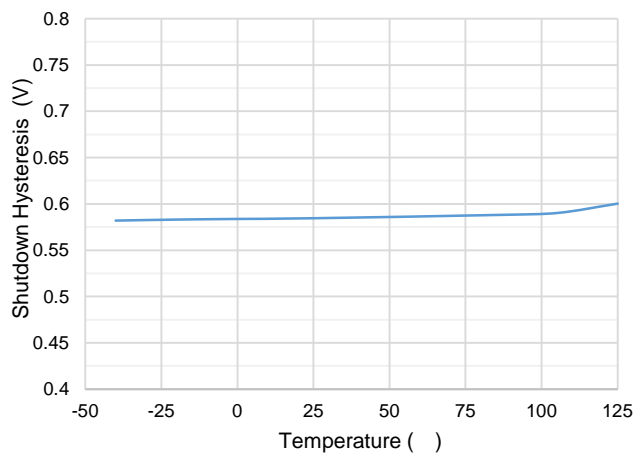


Figure 11. Shutdown Threshold Hysteresis vs. Temperature

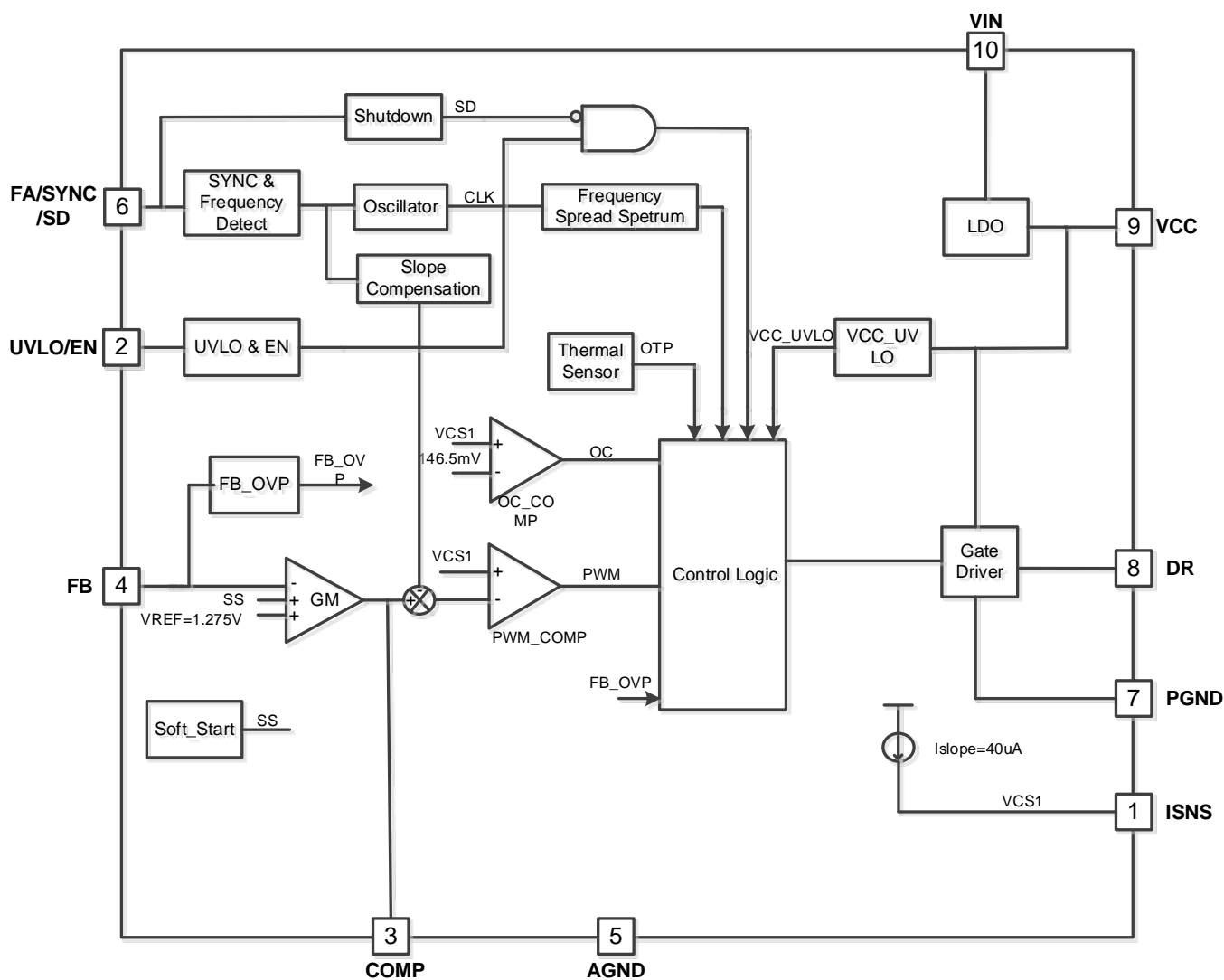


Figure 12. Functional Block Diagram

Overview

The SCT81621 device is a wide input range, non-synchronous boost controller that uses peak-current-mode control. The device can be used in boost, SEPIC, and flyback topologies.

In a typical application circuit, the peak current through the external MOSFET is sensed through an external sense resistor. The voltage across this resistor is fed into the ISNS pin. This voltage is fed into the positive input of the PWM comparator. The output voltage is also sensed through an external feedback resistor divider network and fed into the error amplifier negative input. The output of the error amplifier (COMP pin) is added to the slope compensation ramp and fed into the negative input of the PWM comparator. At the start of any switching cycle, the oscillator sets the RS latch using the switch logic block. This forces a high signal on the DR pin (gate of the external MOSFET) and the external MOSFET turns on. When the voltage on the positive input of the PWM comparator exceeds the negative input, the RS latch is reset and the external MOSFET turns off. The voltage sensed across the sense resistor generally contains spurious noise spikes. These spikes can force the PWM comparator to reset the RS latch prematurely. To prevent these spikes from resetting the latch, a blank-out circuit inside the IC prevents the PWM comparator from resetting the latch for a short duration after the latch is set. This duration is called the blanking interval and is specified as minimum on-time in the Electrical Characteristics section. Under extremely light-load or no-load conditions, the energy delivered to the output capacitor when the external MOSFET is on during the blanking interval is more than what is delivered to the load. An over-voltage comparator inside the SCT81621 prevents the output voltage from rising under these conditions. The over-voltage comparator senses the feedback (FB pin) voltage and resets the RS latch. The latch remains in reset state until the output decays to the nominal value.

The SCT81621 works at Pulse skip mode to further increase the efficiency in light load condition.

The quiescent current of SCT81621 is 415uA typical under no-load condition and no switching. Disabling the device, the typical supply shutdown current on VIN pin is 3.9uA.

Overvoltage Protection

The SCT81621 has over voltage protection (OVP) for the output voltage. OVP is sensed at the feedback pin (FB). If at any time the voltage at the feedback pin rises to 1.36V (typ.), OVP is triggered. OVP will cause the DR pin to go low, forcing the power MOSFET off. With the MOSFET off, the output voltage will drop. The SCT81621 begins switching again when the feedback voltage reaches 1.28V (typ.).

Slope Compensation Ramp

The SCT81621 uses a current mode control scheme. The main advantages of current mode control are inherent cycle-by-cycle current limit for the switch and simpler control loop characteristics. However, current mode control has a Sub-harmonic Oscillation when duty cycle is greater than 50%. To prevent the Sub-harmonic oscillations, a compensation ramp is added to the control signal.

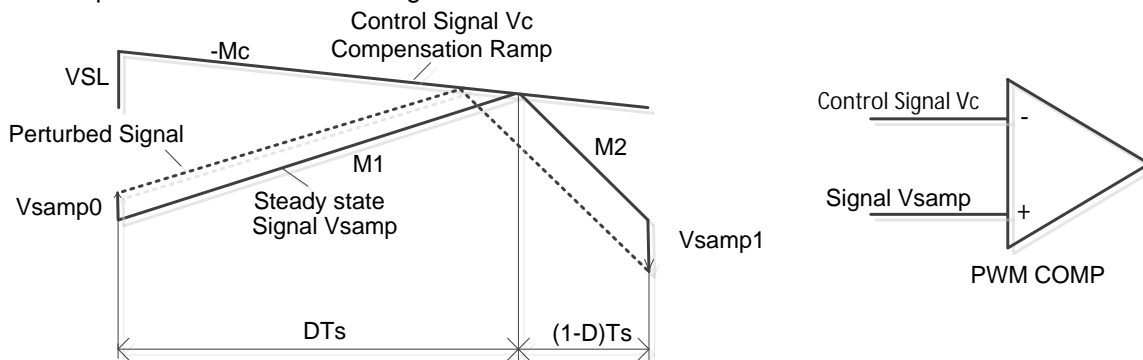


Figure13. Sub-Harmonic Oscillation for $D > 0.5$ and Compensation Ramp to Avoid Sub-Harmonic Oscillation

The current mode control scheme samples the inductor current, I_L , and compares the sampled signal, V_{smp} , to an internally generated control signal, V_c . The current sense resistor, R_{SEN} , as shown in Figure13 converts the sampled inductor current, I_L , to the voltage signal, V_{smp} , that is proportional to I_L such that

$$V_{smp} = I_L * R_{SEN} \quad (1)$$

Figure13 illustrates the theory why Sub-Harmonic Oscillation happens. The rising and falling slopes, M_1 and $-M_2$ respectively, of V_{smp} are also proportional to the inductor current rising and falling slopes, M_{on} and $-M_{off}$ respectively. Where M_{on} is the inductor slope during the switch on-time and $-M_{off}$ is the inductor slope during the switch off-time and are related to M_1 and $-M_2$ by

$$M_1 = M_{on} * R_{SEN} \quad (2)$$

$$-M_2 = -M_{off} * R_{SEN} \quad (3)$$

For the boost topology:

$$M_1 = M_{on} * R_{SEN} = V_{in} * R_{SEN} / L \quad (4)$$

$$M_2 = M_{off} * R_{SEN} = (V_{out} - V_{in}) * R_{SEN} / L \quad (5)$$

In Figure13, a small increase in the load current causes the sampled signal to increase by V_{smp0} . The effect of this load change, V_{smp1} , at the end of the first switching cycle is

$$\Delta V_{smp1} = -\left(\frac{M_2 - M_c}{M_1 + M_c}\right) * \Delta V_{smp0} \quad (6)$$

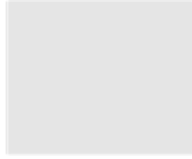
So, When No compensation ramp signal is added, which M_c is zero, then:

$$\Delta V_{smp1} = -\left(\frac{M_2}{M_1}\right) * \Delta V_{smp0} = -\left(\frac{D}{1-D}\right) * \Delta V_{smp0} \quad (7)$$

When $D > 0.5$, V_{smp1} will be greater than V_{smp0} . In other words, the disturbance is divergent. So a very small perturbation in the load will cause the disturbance to increase.

After a compensation ramp is added to the control signal. To ensure that the perturbed signal converges we must maintain:

$$\left| -\left(\frac{M_2 - M_c}{M_1 + M_c}\right) \right|$$



Output Voltage

The output voltage is set by an external resistor divider RFBT and RFBB in typical application schematic. A minimum current of typical 20uA flowing through feedback resistor divider gives good accuracy and noise covering. The value of RFBT can be calculated by Equation 12.

$$R_{FBT} = \frac{V_{OUT} - V_{REF}}{V_{REF}} \times R_{FBB} \quad (12)$$

where:

- V_{REF} is the feedback reference voltage

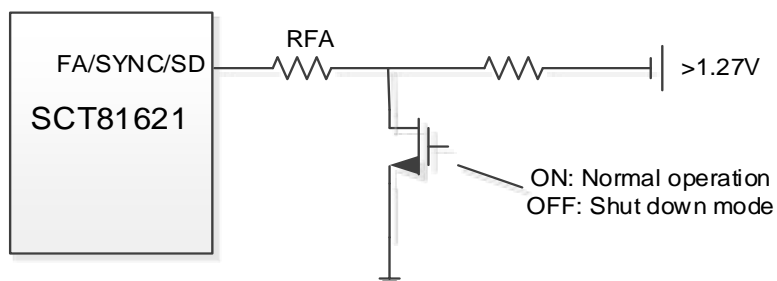


Figure18. Shutdown operation in Frequency Adjust Mode

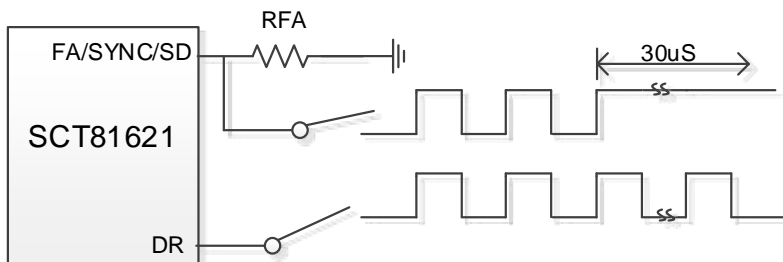


Figure19. Shutdown operation in Frequency Synchronization Mode

Enable and Under Voltage Lockout Threshold

The external UVLO resistor divider must be designed so that the voltage at the UVLO pin is greater than 1.42 V (typical) when the input voltage is in the desired operating range. The values of R1 and R2 can be calculated as shown in Equation 14 and Equation 15.

$$R1 = \frac{V_{IN(ON)} - V_{IN(OFF)}}{I_{UVLO}} \quad (14)$$

where

- $V_{IN(ON)}$ is the desired start-up voltage of the converter
- $V_{IN(OFF)}$ is the desired turnoff voltage of the converter.

$$R2 = R1 * \frac{V_{UVLOEN}}{V_{IN(ON)} - V_{UVLOEN}} \quad (15)$$

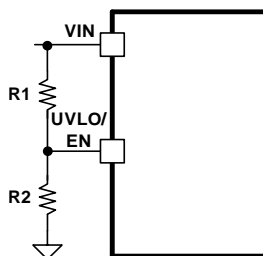


Figure20. System UVLO Resistor Divider

Frequency Spread Spectrum

To reduce EMI, the device implements Frequency Spread Spectrum (FSS). The FSS circuitry shifts the switching frequency of the regulator periodically within a certain frequency range around the adjusted switching frequency. The jittering span is $\pm 6\%$ of the switching frequency with $1/512$ swing frequency. This frequency dithering function is effective for both frequency adjusted by resistor placed at FA/SYNC/SD pin and an external clock synchronization application.

Typical Application (Boost)

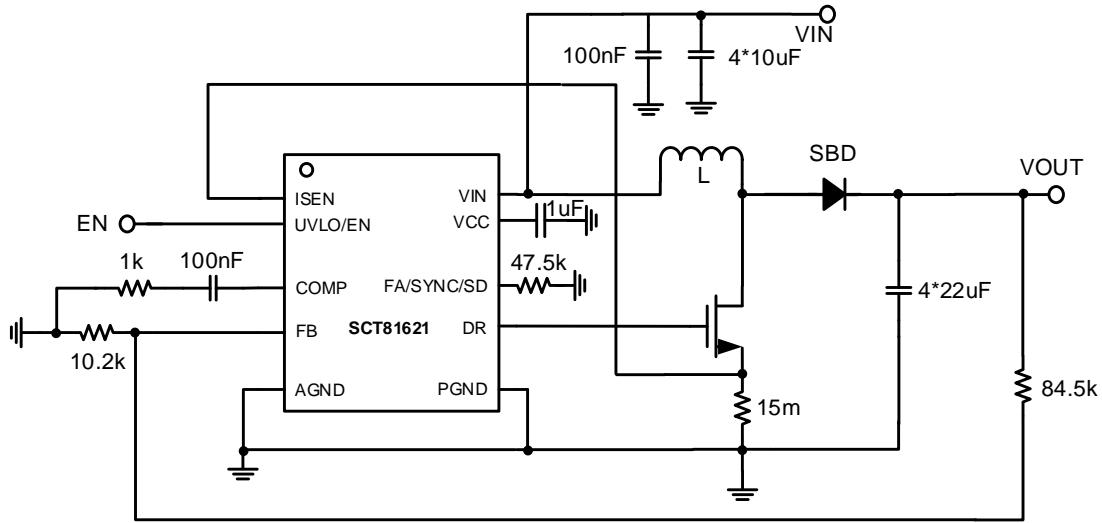


Figure 21. Application Schematic, 3V to 11V, 2A Boost Regulator at 400kHz

Design Parameters

Design Parameters	Example Value
Input Voltage	5V Normal 3V to 11V
Output Voltage	12V
Maximum Output Current	3A
Switching Frequency	400 KHz
Output voltage ripple (peak to peak)	75mV (Load=2A)

Inductor Selection (Boost)

The performance of inductor affects the power supply's steady state operation, transient behavior, loop stability, and boost converter efficiency. The inductor value, DC resistance, and saturation current influences both efficiency and the magnitude of the output voltage ripple. Larger inductance value reduces inductor current ripple and therefore leads to lower output voltage ripple. For a fixed DC resistance, a larger value inductor yields higher efficiency via reduced RMS and core losses. However, a larger inductor within a given inductor family will generally have a greater series resistance, thereby counteracting this efficiency advantage.

Inductor values can have $\pm 20\%$ or even $\pm 50\%$ tolerance with no current bias. When the inductor current approaches saturation level, its inductance can decrease 20% to 35% from the value at 0-

The total power dissipation of MOSFET includes conduction loss as shown in the first term and switching loss as shown in the second term. The total power dissipation should be within package thermal ratings.

Output Diode Selection

Observation of the boost converter circuit shows that the average current through the diode is the average load current, and the peak current through the diode is the peak current through the inductor. The diode should be rated to handle more than its peak current. The peak diode current can be calculated using Equation 26.

$$I_{D(PEAK)} = \frac{I_{OUT}}{(1-D)} + \Delta I_L \quad (26)$$

Thermally the diode must be able to handle the maximum average current delivered to the output. The peak reverse voltage for boost converters is equal to the regulated output voltage. The diode must be capable of handling this voltage. To improve efficiency, a low forward drop schottky diode is recommended.

Application Waveforms

Vin=5V, Vout=12V, unless otherwise noted

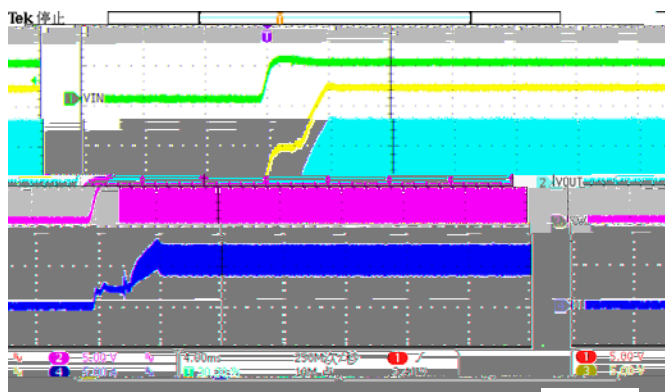


Figure 22. Power up(Iload=2A)



Figure 23. Power down(Iload=2A)

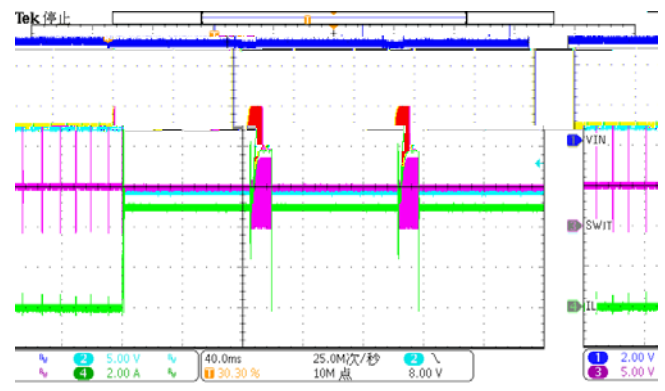


Figure 24. Over current protection (Iload=5A)

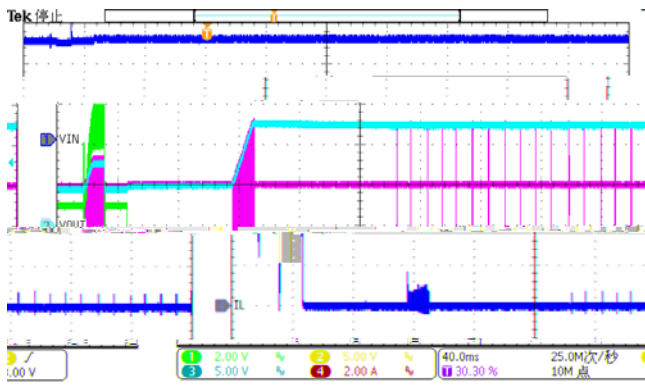


Figure 25. Over current recovery (Iload=5A)

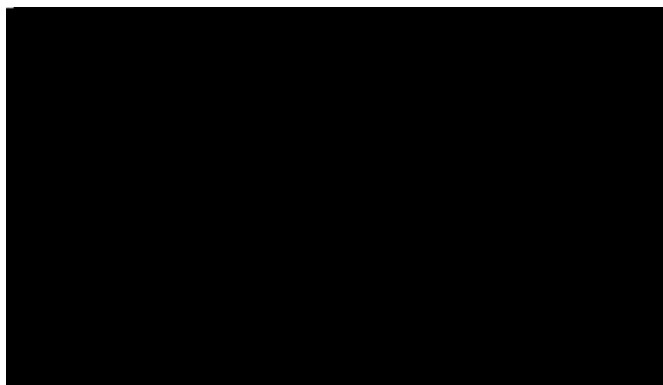


Figure 26. Steady-state (Iload=2A)

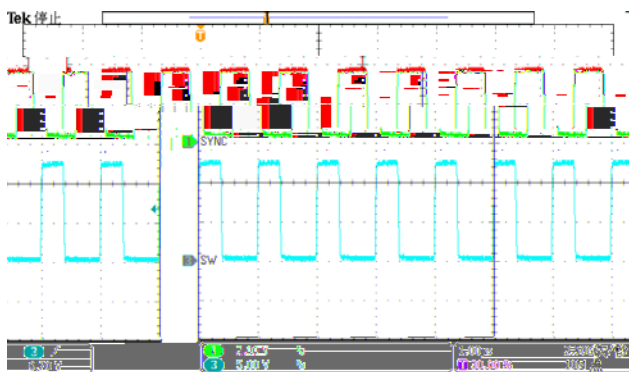
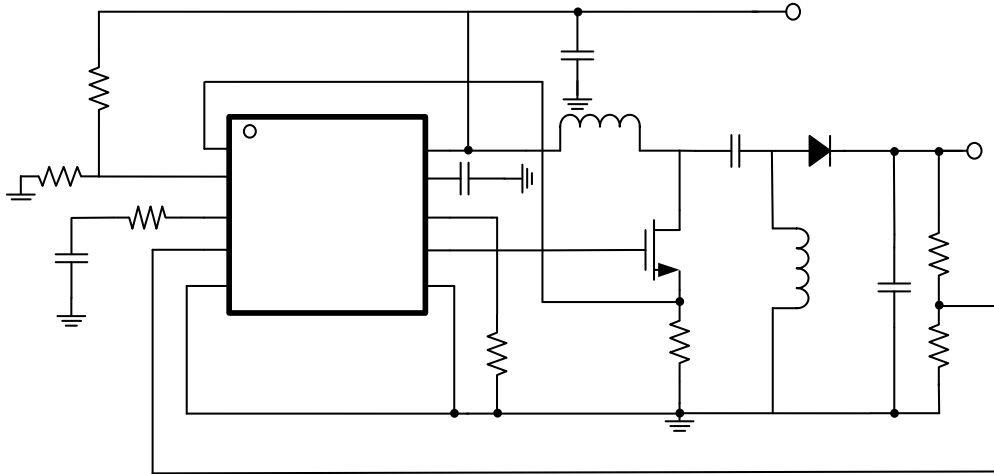


Figure 27. Sync Frequency

Typical Application(Sepic)



Inductor Selection (Sepic)

A good rule for determining the inductance to use is to allow the inductor peak-to-peak ripple current to be approximately 20% to 40% of the maximum input current at the minimum input voltage. The current ripple flowing in inductors L1 and L2 is given by:

$$\Delta I_{L1} = I_{IN} \times 40\% = I_O \times \frac{V_O}{V_{IN_MIN}} \times 40\% \quad (27)$$

$$\Delta I_{L2} = I_O \times 40\% = I_O \times 40\% \quad (28)$$

Normally we can select equal value for the inductors L1 and L2, derived as:

$$L_1 = L_2 = L = \frac{V_{IN_MIN}}{\Delta I_L \times f_{SW}} \times D_{MAX} \quad (29)$$

Where

- f_{SW} is the switching frequency.

Note that the saturation current of inductors should be greater than peak current flowing in inductors, given by:

$$I_{L1_PEAK} = I_{IN} + \frac{\Delta I_L}{2} = I_O \times \frac{V_O}{V_{IN_MIN}} \times (1 + \frac{40\%}{2}) \quad (30)$$

$$I_{L2_PEAK} = I_O + \frac{\Delta I_L}{2} = I_O \times (1 + \frac{40\%}{2}) \quad (31)$$

If L1 and L2 are wound in same core as a coupled inductor, the inductance required will be half due to the mutual induction, calculated by:

$$L_1 = L_2 = \frac{L}{2} = \frac{V_{IN_MIN}}{2 \times \Delta I_L \times f_{SW}} \times D_{MAX} \quad (32)$$

Power MOSFET Selection

The following parameters should be taken into consideration for MOSFET: the on-resistance R_{DS_ON} , the minimum gate threshold voltage V_{TH_MIN} , the total gate charge Q_g , the reverse transfer capacitance C_{RSS} , and the maximum drain to source voltage V_{Q_MAX} . The peak switching voltage between drain to source in a SEPIC is given by:

3 _

Output Diode Selection

The diode at the output side must withstand the reverse voltage when the MOSFET is turned-on. The peak reverse voltage is given by:

$$V_{D_PEAK} = V_{IN_MAX} + V_{O_MAX} \quad (37)$$

The diode should also be capable to flow switch peak current I_{Q_PEAK} .

The power dissipation of the diode is equal to the forward voltage drop multiplies output current. Schottky diodes are recommended here to minimize the power loss.

Coupling Capacitor Selection

For ceramic capacitors with low-ESR, the peak to peak voltage ripple on coupling capacitor is estimated by:

$$\Delta V_{CS} = \frac{I_O \times D_{MAX}}{C_S \times f_{SW}} \quad (38)$$

The maximum voltage across the coupling capacitor is maximum input voltage. The voltage rating of the coupling capacitor must be greater than it.

The RMS current of coupling capacitor is given by:

$$I_{CS_RMS} = I_O \times \sqrt{\frac{V_O + V_D}{V_{IN_MIN}}} \quad (39)$$

There is a large RMS current through coupling capacitor relative to output power. Ensure the coupling capacitor can withstand it with good heat generation to have proper thermal performance.

Input Capacitor Selection

The SEPIC has an inductor at input side thus the input current is continuous and triangular. The RMS current flowing through the input capacitor is given by:

$$I_{IN_RMS} = \frac{\Delta I_{L1}}{\sqrt{12}} \quad (40)$$

Since input current ripple is relative low, the capacitance would be not too critical. While 100 F in total or higher value is strongly recommended in order to provide stable input supply.

Output Capacitor Selection

Similar to boost converter, the SEPIC output capacitor suffers large current ripple. The capacitance must be enough to provide the load current. The maximum voltage ripple in the output capacitor is:

$$V_{OUT} = \frac{I_O \times D_{MAX}}{C_{OUT} \times f_{SW}} + \frac{ESR \times (I_{L1_PEAK} + I_{L2_PEAK})}{C_{OUT} \times f_{SW}}$$

Application Waveforms

$V_{in}=5V$, $V_{out}=12V$, unless otherwise noted

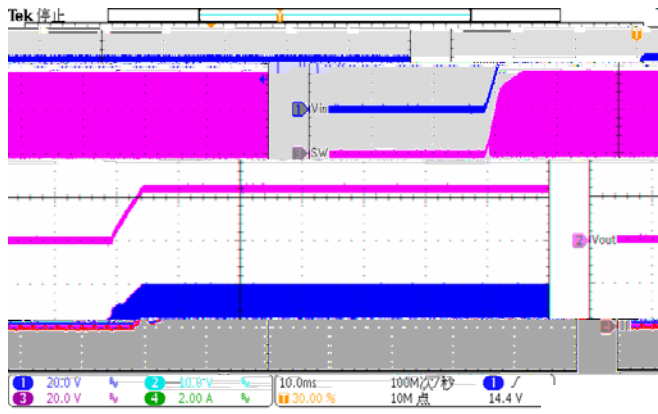


Figure 30. Power up($I_{load}=2A$)

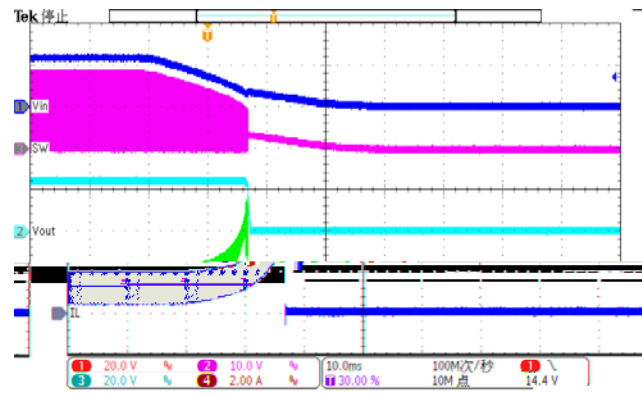


Figure 31. Power down($I_{load}=2A$)

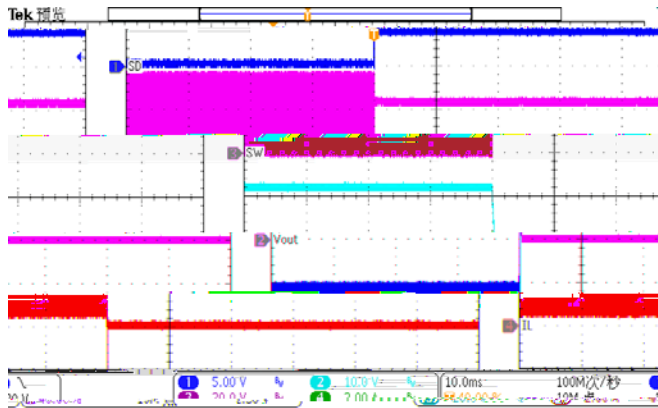


Figure 32. Shutdown entry

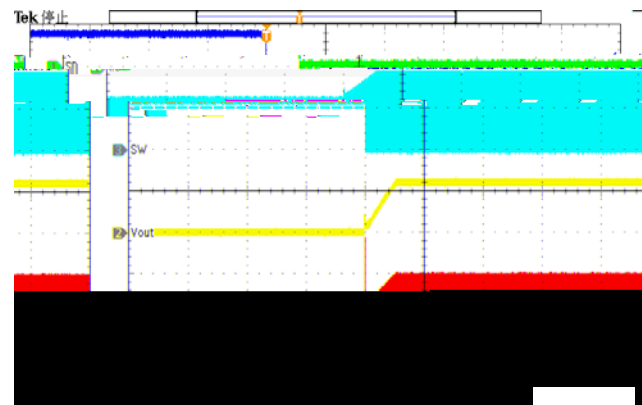


Figure 33. Shutdown remove

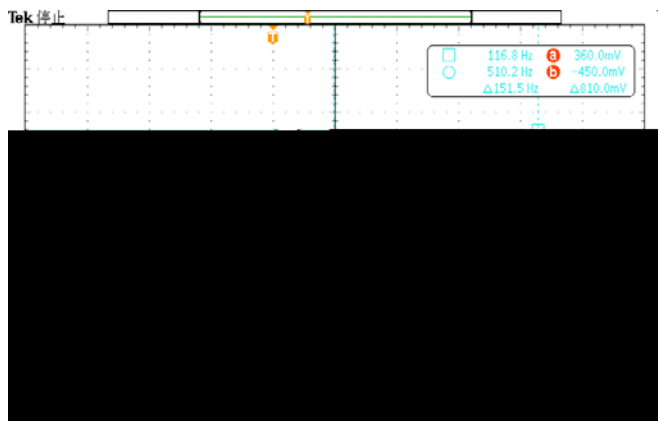


Figure 34. LoadTrans ($I_{load}=0.5A-1.5A$)

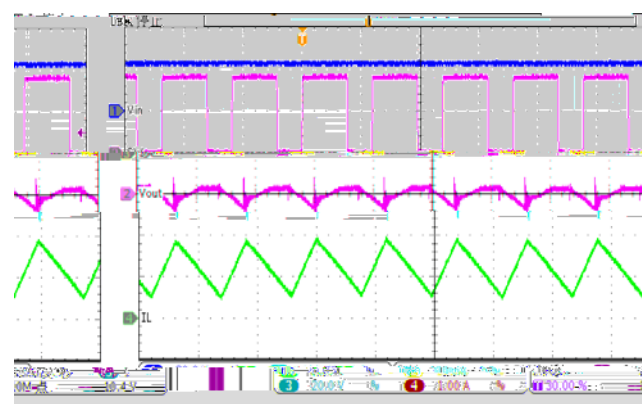
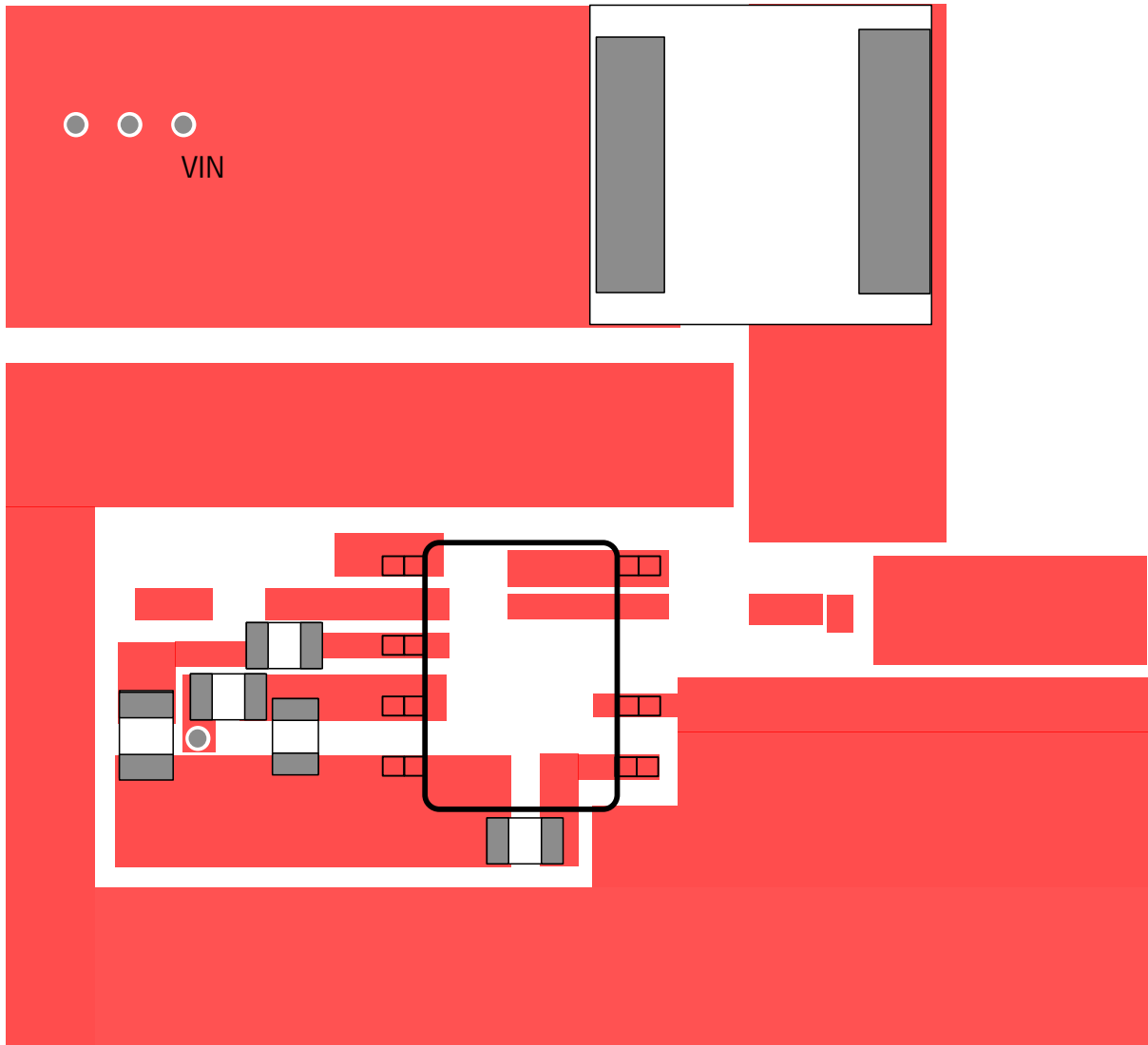
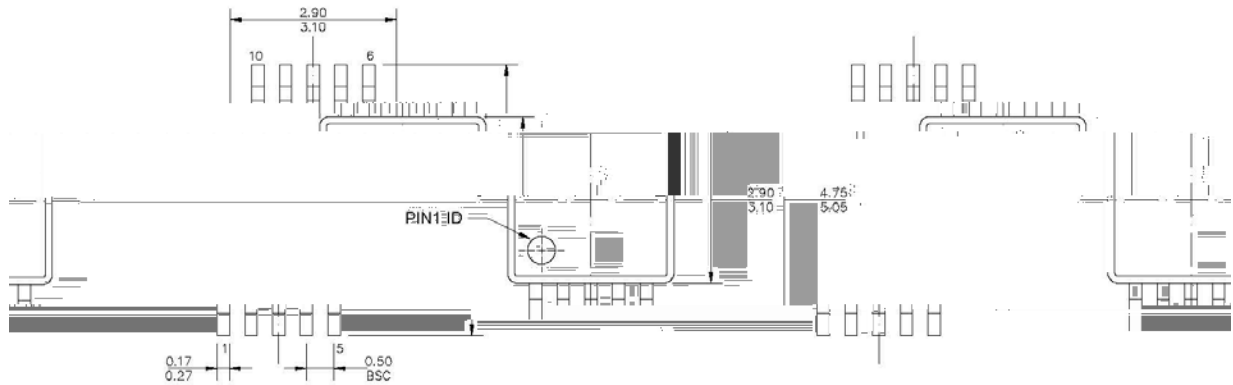


Figure 35. steady-state ($I_{load}=2A$)

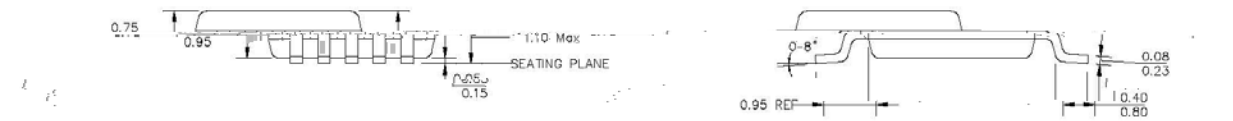
Layout Guideline





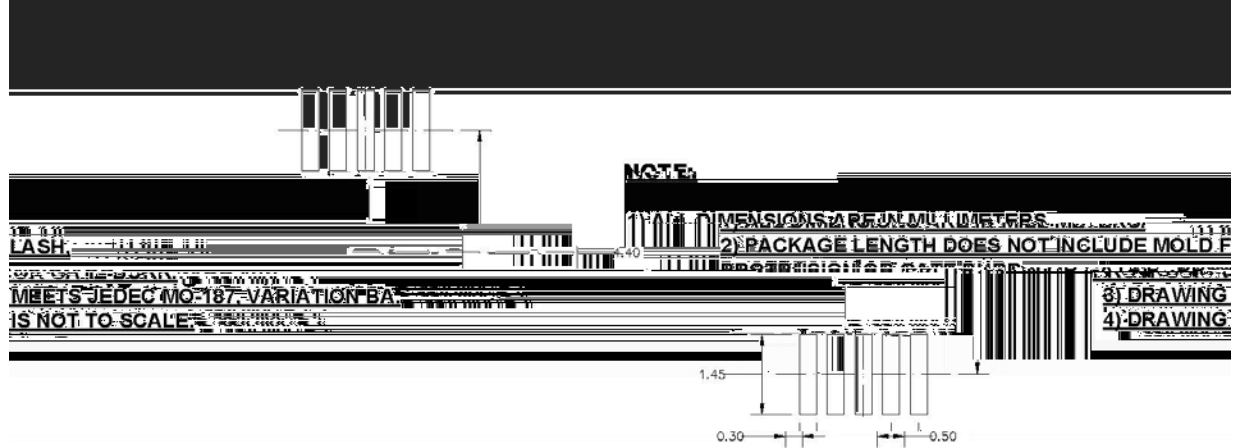
TOP VIEW

BOTTOM VIEW



FRONT VIEW

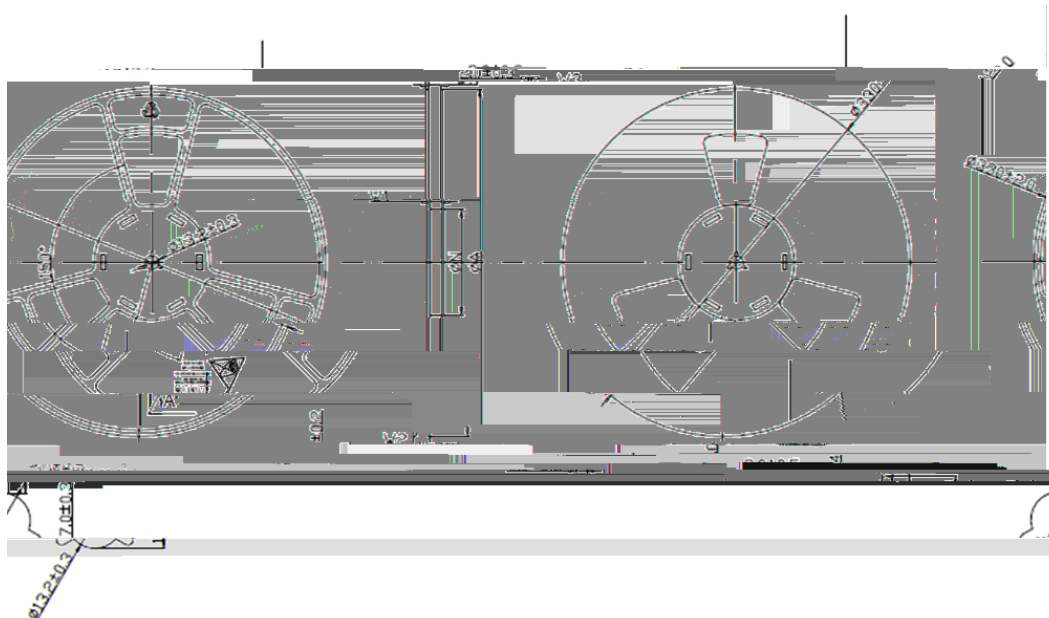
SIDE VIEW



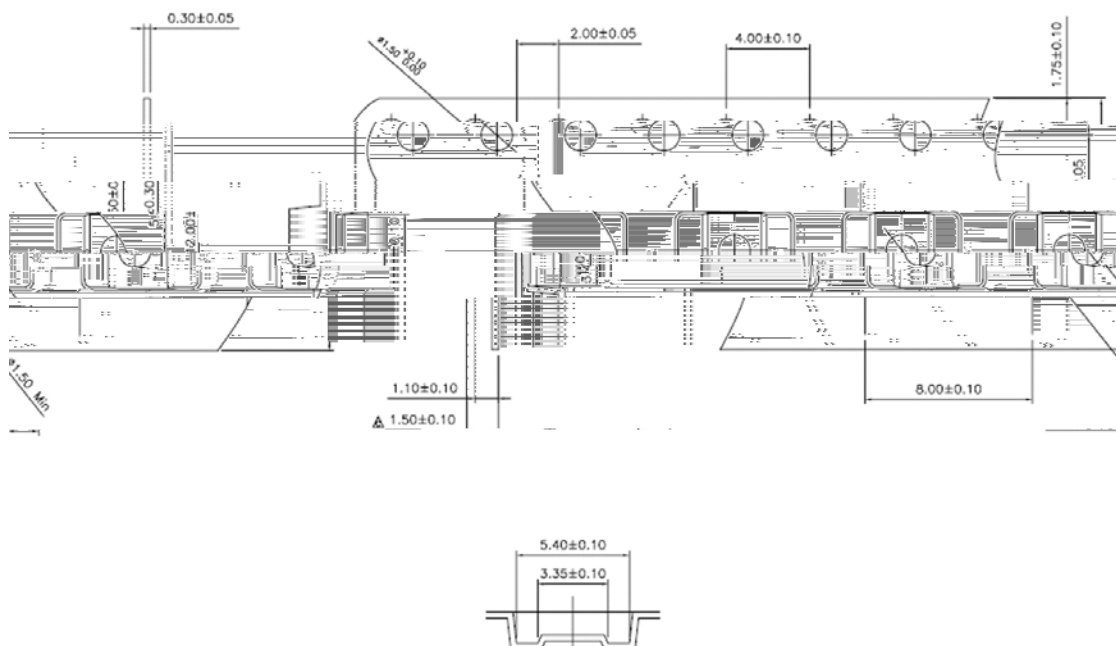
RECOMMENDED LAND PATTERN

SCT81621

Orderable Device	Package Type	Pins	SPQ
SCT81621MRDR	MSOP	10	4000



T SPECIFICATIONS				PRODUCT	
IN	W1(+20)	W2(Max)	W3(Max)	TYPE WIDTH	ØA



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